

In a method of forming a fine pattern, a silicon-oxide-based film is formed directly or by way of another layer on a substrate or on an underlying layer. The silicon-oxide-based film is formed such that nitrogen content of the surface thereof assumes a value of 0.1 atm.% or less. A chemically-amplified photoresist layer is formed on the silicon-oxide-based film. A mask pattern of a mask is transferred onto the chemically-amplified photoresist layer upon exposure through the mask. Thus, there is prevented generation of a tapered corner in a portion of a resist pattern in the vicinity of a boundary area between the resist pattern and a substrate.